

(19)  
(12)

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G02F 1/1335

(11)  
(43)

2001 - 0107688  
2001 12 07

(21) 10 - 2001 - 0028415  
(22) 2001 05 23

(30) 2000 - 153508 2000 05 24 (JP)

(71) 가 가

1 1 1

(72) 1 9 2 가 가

1 9 2 가 가

(74)

:

(54)

가 , , , 1 , 1  
(出光) , . (圓偏光)  
(peak)

1 가 , 1

1



34 - - , 35 - - ,  
 36 - - , 37 - - ,  
 38 - - (passivation) , 39 - - ,  
 40 - - (contact hole), 41 - - ,  
 42 - - ( ), 43 - - ,  
 50 - - .

(back light)  
 50%

( half mirror))  
 가

(pin hole)

가

가

가

가

가

가

(front light)

(導光板)

(線光源)

가



( )

,

1 4 (15) 2 (13, 14) (13)

/2 (12) (11) (14)

/4 (25) (26) (21)

(Indium Tin Oxide) (13) (50) ITO

(polymer) (16) (14) (18) (17)

(12) (retarder) (15) 가 가

가

2 3 (13) (32) (33) (32)

(34) (34) ( , TFT ; 31)가 (1

6) (32) (34) (35) .

TFT(31) (35) (33) (a - Si) (36),

ation) (38) (37) (41) (39) (passiv

(33) (36) (bottom gate) TFT (13)

TFT(31) (33) (36)

,

(16) (50) 10 $\mu$ m (contact hole; 40) (41)

(magenta), (50) (50) , , 3

(16) (17) (15) 3 가 (加法混色)

(16) (32), (34), (21)

(14) (14) (16)

ITO (17) (14) (

17) (18)

(17) (mask sputter) (patterning)

(17) (18)

(13) (14) (15)  
 (15) 가  
 (13) (14) 가

(13) (14) (18) ( ; 42) (43) (43)  
 가 (overcoat) 가 1 (18) (18)

(14) (21) (22)  
 (24) (23)

MIM(Metal Insulator Metal) a-Si TFT  
 2 P-Si

5 (左圖) (右圖) (18) (主面)(18f)  
 (18b) 가 (18f)  
 5 (L1, L2, L1', L2') (18) (

18F) np (18) ( ) (19) (pitch; p) (n)  
 (18b) (19)가 (18f)

np ( ) ( ) ( )  
 (18) (18b) 100% (Lb) 10%

0) (18) 가 (on) , 1 가 (Von ) (15) (2  
 ematic) (13) (14) (n  
 homogeneous)

(12) 가 (Lf) (11) /4  
 (15) (15)

/2

(18) , (15) /2 (11)  
(11) , (開) 가

, 6 (15) (13, 14) 가 (off) ( (零) ; Vo  
ff ) , (15)

, , Von 가 (11) /4 (12)  
, (15) , (15)  
(25) (18) (26) , (18) , (Lf)  
가

, (18) (21)

1 Von , (21) (Lb) (26) (25)  
, ( 10%) (18)  
/4 (12) , (15) ,  
, (11)  
가

, 6 Voff , (21) (18) /4 (12)  
(15) , (11) (11)

, (p) (n) , (np) 가 (18)  
(p)가 ,

, (18) (21) 3 , 3 430n  
m , 550nm 610nm 가 (21) (18) 3  
20~30nm ( , (slit) ) 3

7 가 (18) 가

가 , 가  
(18) (21) 3

가

가 (simulation) (18)  
 (21) 3  
 30~70%

,가

(18) 7

2

2 (18) 8  
 (21) 3  
 1 가 3

(18) (18)

( )

$$= np(1 - \cos \theta) \dots (1)$$

(18) 가 (18)

3 430, 550, 610nm 30° (1)

$$n \cdot \sin \theta = n' \cdot \sin \theta' \dots (2)$$

, n n' (15) (18) (1) (2) (18)  
 24.6nm, 31.5nm, 34.9nm

(18) 8  
 30° (21) 3 30°  
 3 (cover) 30°

, 2

가

, 3 , 30~80nm 가

, 9

3

3

3

1

2

(18) (R), (G), (B) (50)

(50) 10 3

10 (50) (18) 「  
 」  
 (50) 3 (18) 2  
 (50) (18) 1  
 , R, G, B  
 (50)  
 , 10 (50) 가  
 , 3 R, G, B 가 (50) , Y, C, M (減法混色系)  
 가  
 (18) T 가  
 $T^2 (< T)$  가  
 , 2, 3 (21) 3 가 가  
 (18)?d1020010107687? 430nm, 550nm, 610nm  
 , 3  
 , 1 2 4 가

(57)

1.

1 가 1  
 1 가 1

가

1

1

2.

1 ,

1

1  
30~70%

,

3.

1 ,

1

4.

1 ,

5.

4 ,

0nm~40nm

6.

4 ,

30nm~80nm

7.

4 ,

1

8.

,

1

,

1

가

,

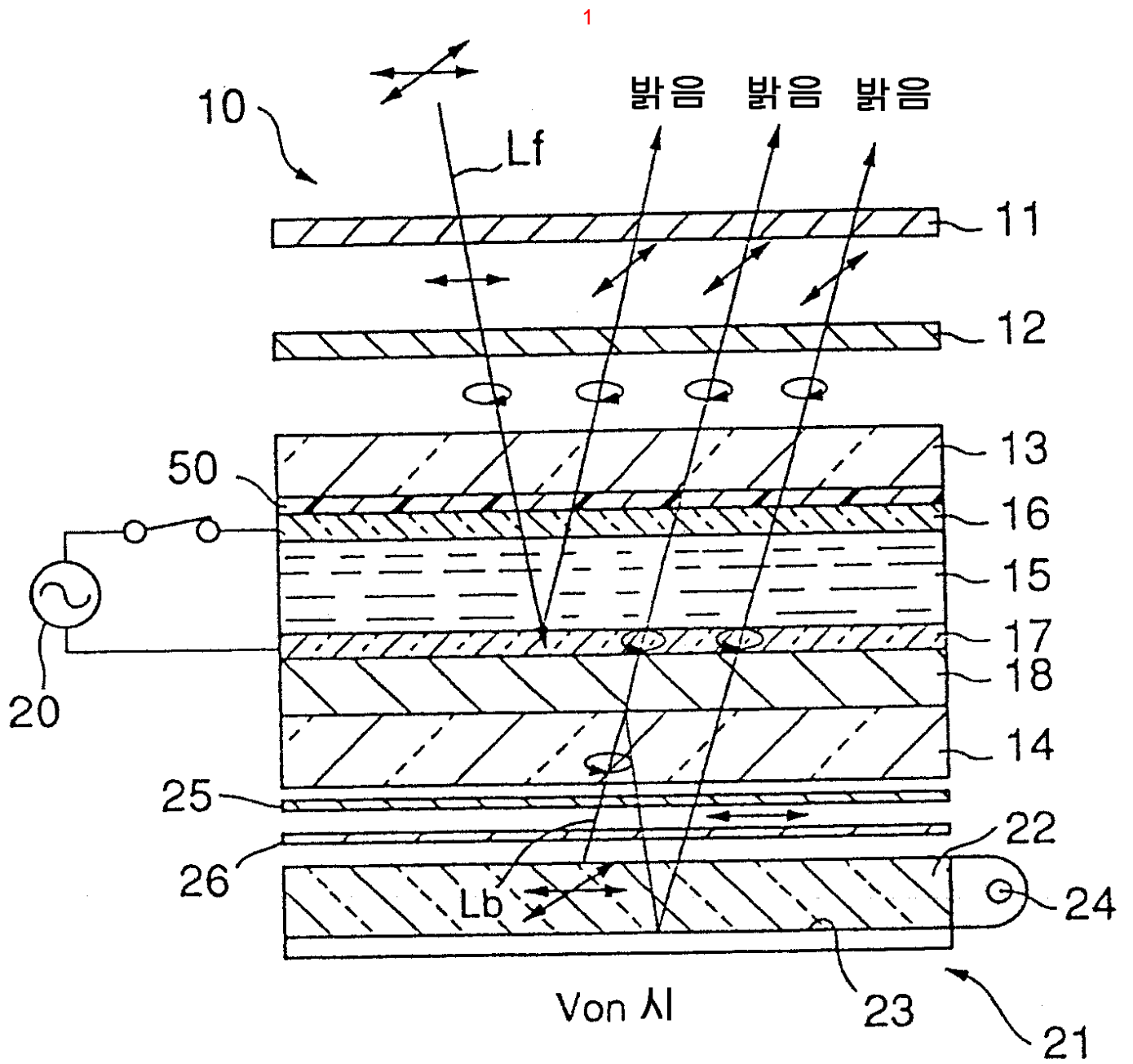
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,

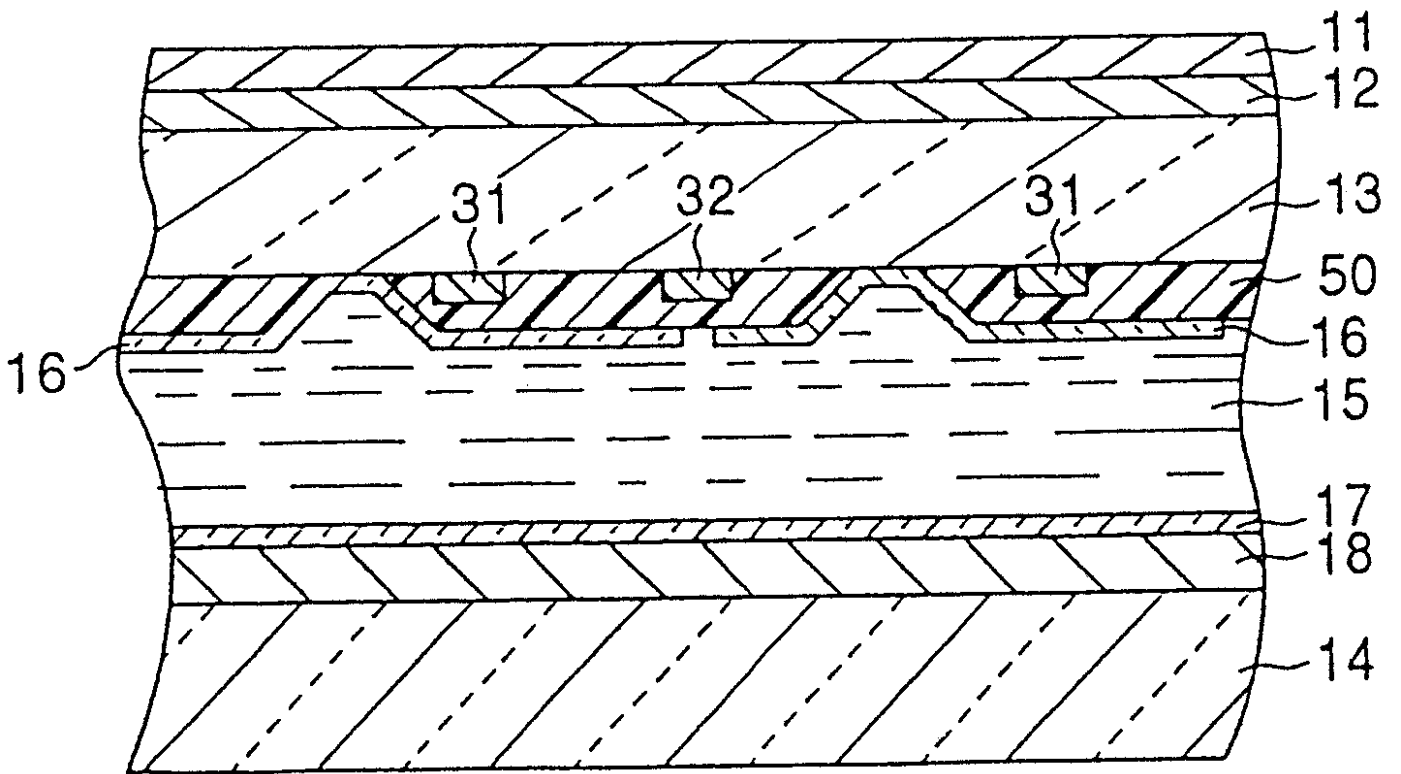
가

1

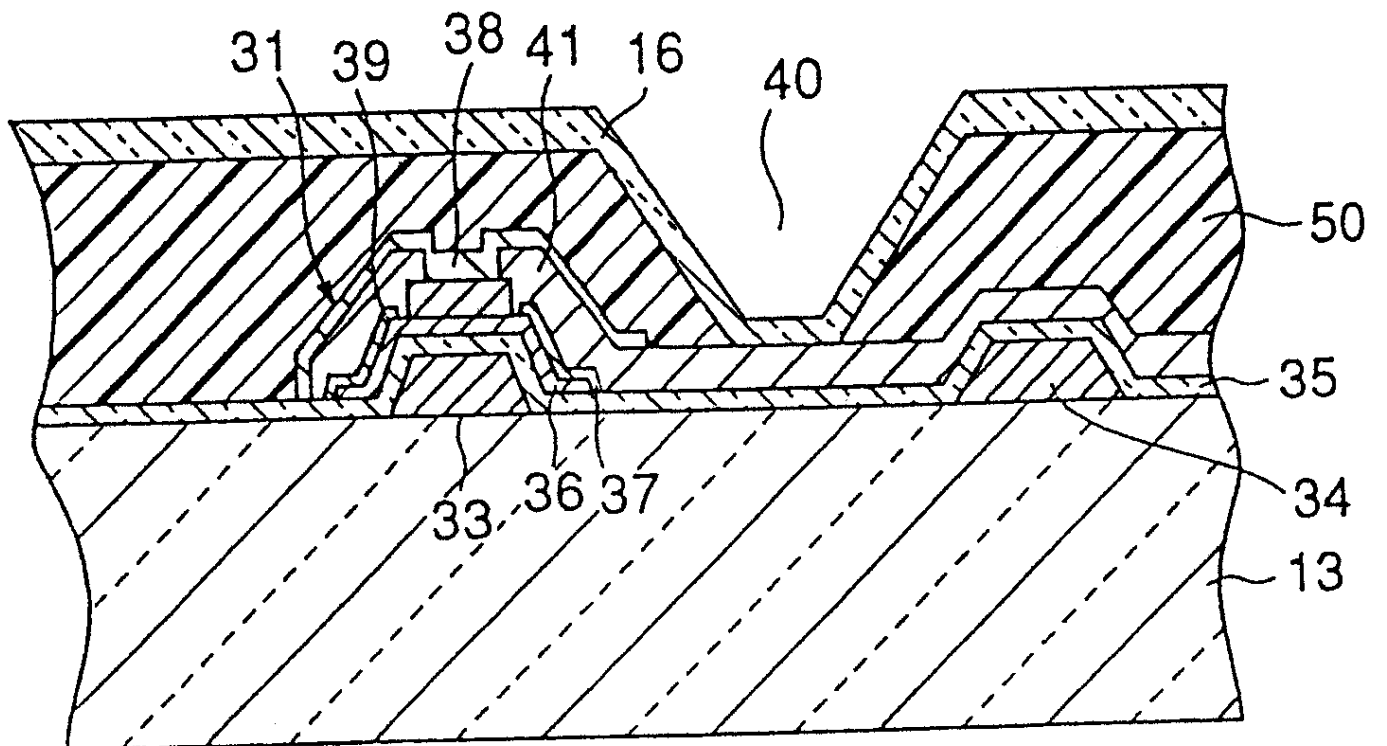
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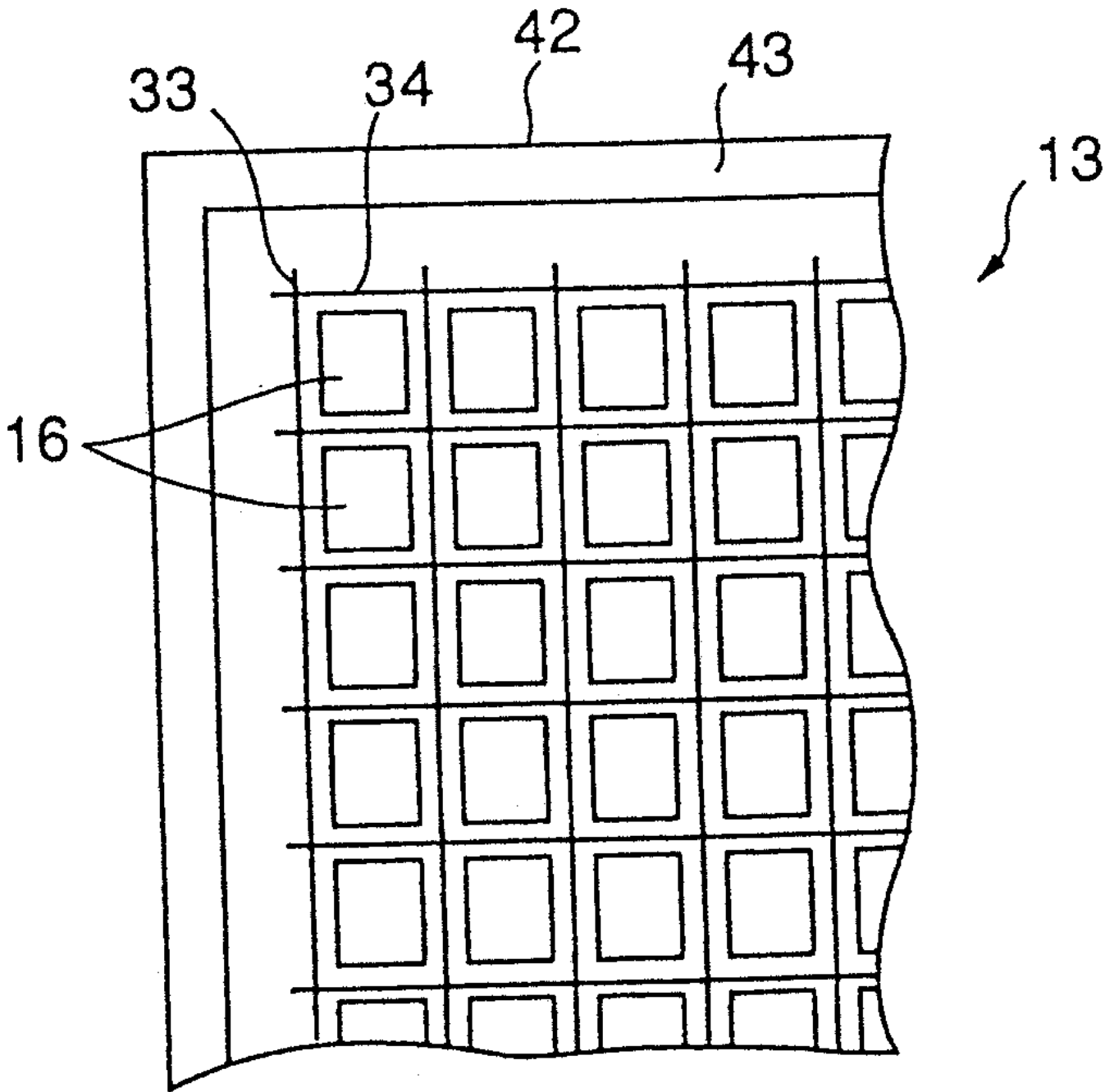
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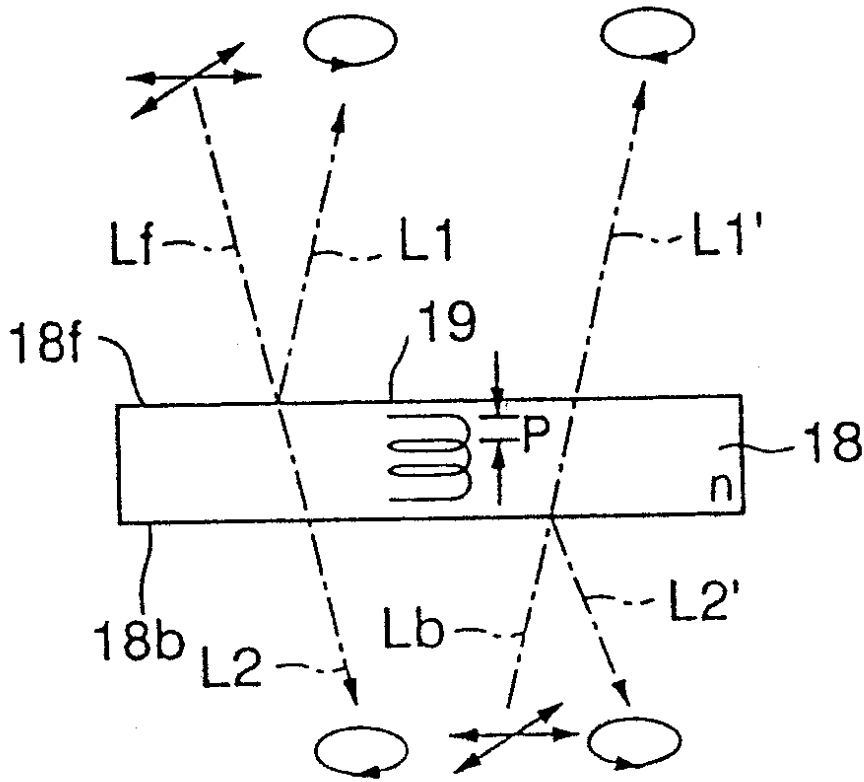
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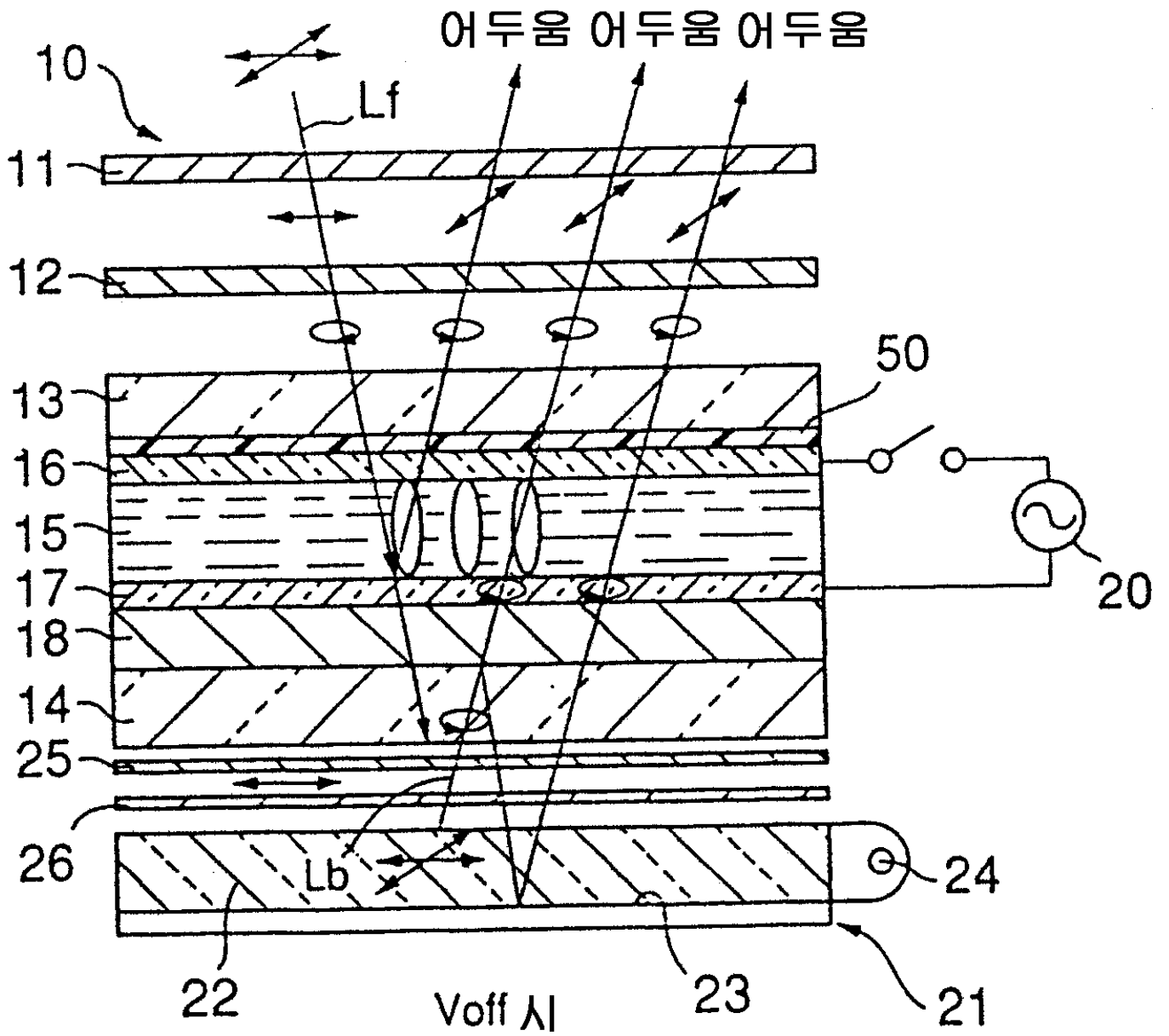
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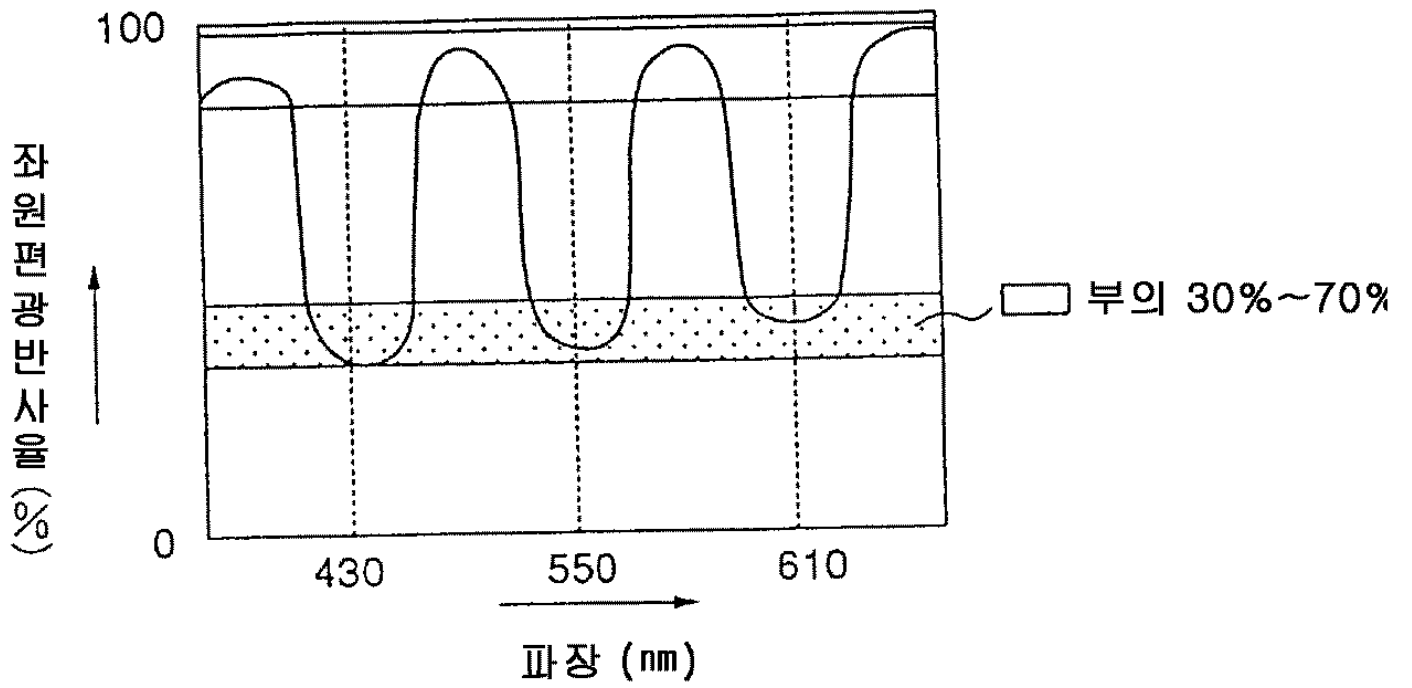
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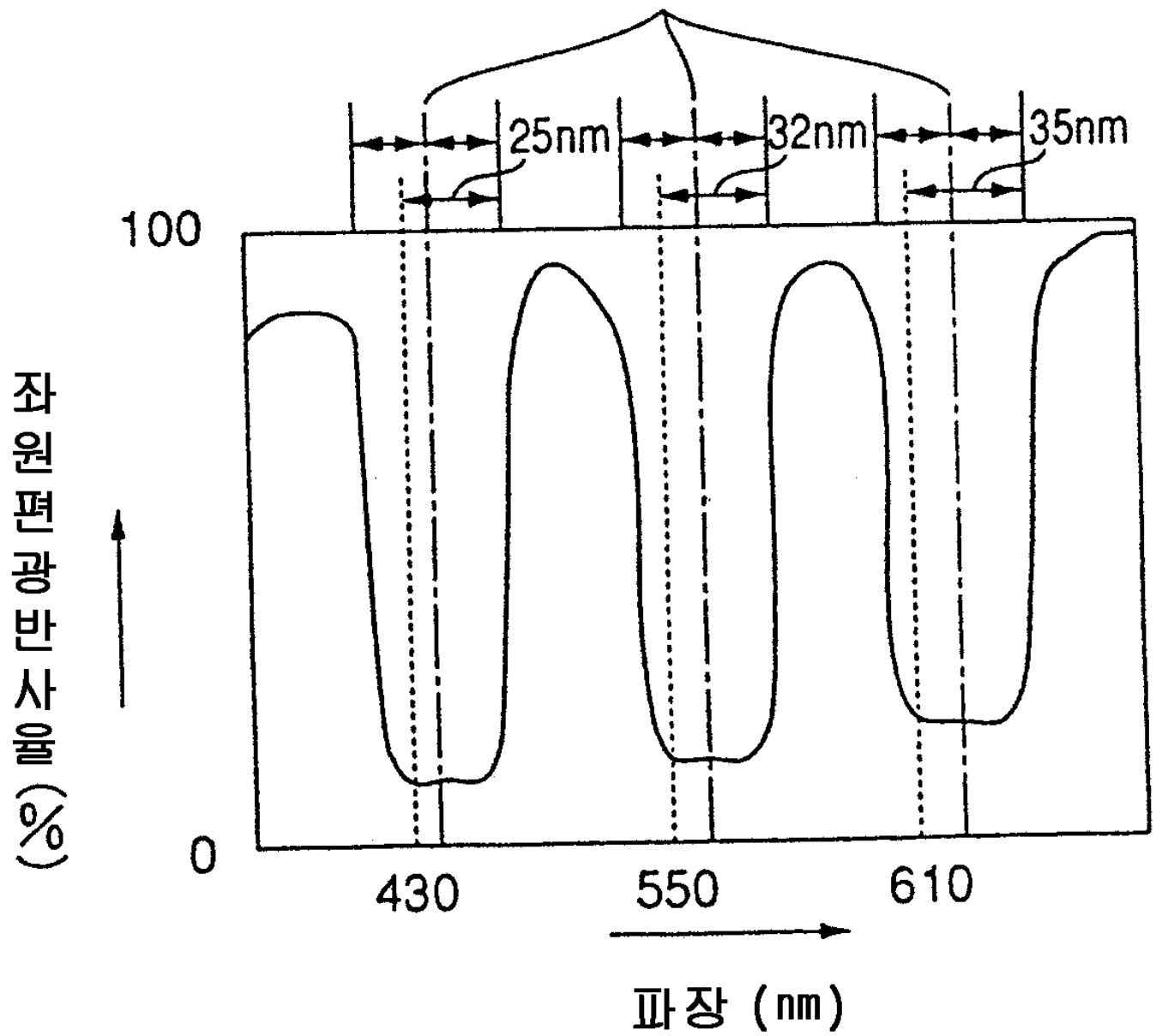
-  : 자연광
-  : 우원편광
-  : 좌원편광

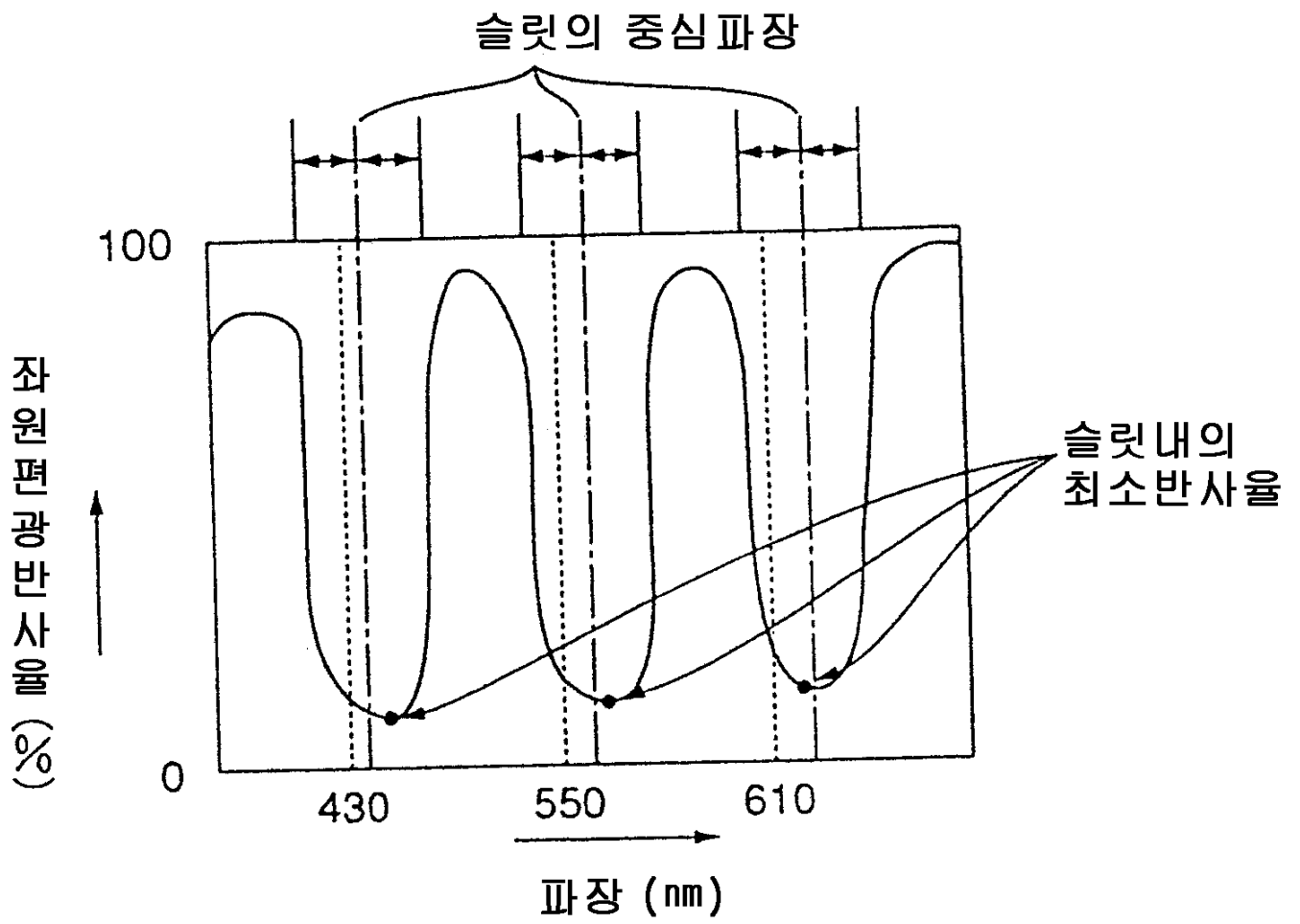


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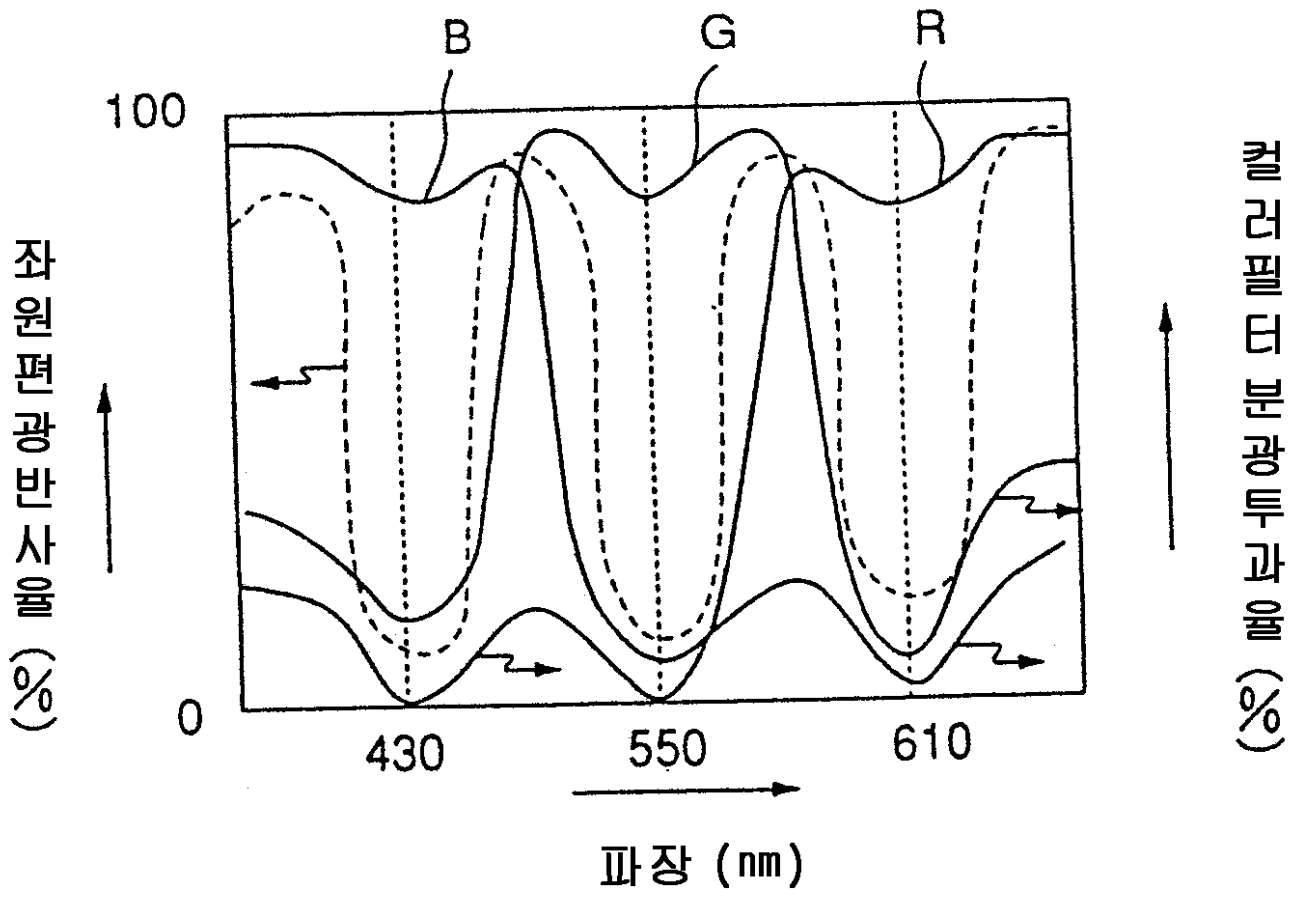


## 슬릿의 중심파장





10



专利名称(译)	透反液晶显示元件		
公开(公告)号	<a href="#">KR1020010107688A</a>	公开(公告)日	2001-12-07
申请号	KR1020010028415	申请日	2001-05-23
[标]申请(专利权)人(译)	株式会社东芝		
申请(专利权)人(译)	Sikki东芝股份有限公司		
当前申请(专利权)人(译)	Sikki东芝股份有限公司		
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发明人	오타케도시아 히사타케유조		
IPC分类号	G02F1/1335 G02F1/13357 G02F1/13363 G02F1/139 G09F9/00 G09F9/30		
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代理人(译)	KIM , YOON BAE		
优先权	2000153508 2000-05-24 JP		
其他公开文献	KR100427881B1		
外部链接	<a href="#">Espacenet</a>		

摘要(译)

本发明的液晶显示装置配备有后面布置的背光，并且根据其辐射液晶层的施加电压调制入射光，并且布置的光在多个上具有各自的强度峰值。选择性反射层的固定小波，其选择性地反射第一偏振片的液晶层和选择性反射层的入射光的第一圆偏振分量，其沿着该极轴传输线性偏振，其具有极轴和第一个偏光板。当选择性反射层将可见光的波长范围划分为多个小区域时，朝向多个指定波长区域的所述第一圆偏振分量的反射率小于多个指定波长区域的每个区域，其中每个指定波长区域包括一个强度峰值。而不是关于短波长和长波长区域的所述第一圆偏振分量的反射率。

